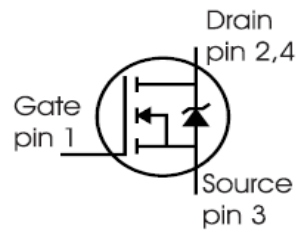
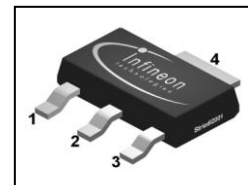


**OptiMOS™ Small-Signal-Transistor**
**Features**

- N-channel
- Enhancement mode
- Avalanche rated
- Qualified according to AEC Q101
- 100% lead-free; RoHS compliant
- Halogen-free according to IEC61249-2-21


**Product Summary**

$V_{DS}$	100	V
$R_{DS(on),max}$	0.24	$\Omega$
$I_D$	1.8	A


**PG-SOT223**


Type	Package	Tape and Reel Information	Marking	Halogen-Free	Packing
BSP373N	SOT223	H6327: 1000 pcs/ reel	BSP373N	Yes	Non dry

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_A=25\text{ °C}$	1.8	A
		$T_A=70\text{ °C}$	1.5	
Pulsed drain current	$I_{D,pulse}$	$T_A=25\text{ °C}$	7.3	
Avalanche energy, single pulse	$E_{AS}$	$I_D=1.8\text{ A}$ , $R_{GS}=25\ \Omega$	33	mJ
Reverse diode $dv/dt$	$dv/dt$	$I_D=1.8\text{ A}$ , $V_{DS}=80\text{ V}$ , $di/dt=200\text{ A}/\mu\text{s}$ , $T_{j,max}=150\text{ °C}$	6	kV/ $\mu\text{s}$
Gate source voltage	$V_{GS}$		$\pm 20$	V
Power dissipation <sup>1)</sup>	$P_{tot}$	$T_A=25\text{ °C}$	1.8	W
Operating and storage temperature	$T_j$ , $T_{stg}$		-55 ... 150	$^{\circ}\text{C}$
ESD Class		JESD22-A114 -HBM	0 (<250V)	
Soldering Temperature			260 $^{\circ}\text{C}$	
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance junction - soldering point	$R_{thJS}$		-	-	25	K/W
Thermal resistance junction - ambient	$R_{thJA}$	minimal footprint	-	-	110	
		6 cm <sup>2</sup> cooling area <sup>1)</sup>	-	-	70	

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}\text{ V}, I_D=218\text{ }\mu\text{A}$	2.1	3.0	4.0	
Drain-source leakage current	$I_{DSS}$	$V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	-	0.1	$\mu\text{A}$
		$V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ °C}$	-	-	10	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	10	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=1.8\text{ A}$	-	177	240	m $\Omega$
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=1.5\text{ A}$		3.23	-	S

<sup>1)</sup> Device on 40mm x 40mm x 1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70 $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	199	265	pF
Output capacitance	$C_{oss}$		-	36	48	
Reverse transfer capacitance	$C_{rss}$		-	14	21	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$ $I_D=1.8\text{ A}, R_G=6\ \Omega$	-	4.6	6.9	ns
Rise time	$t_r$		-	5.9	8.91	
Turn-off delay time	$t_{d(off)}$		-	21.9	32.9	
Fall time	$t_f$		-	13.5	20.3	

**Gate Charge Characteristics**

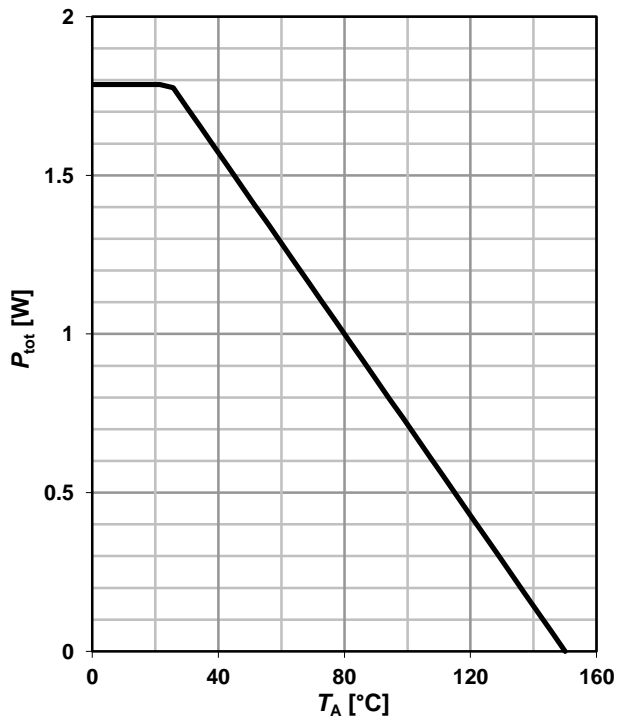
Gate to source charge	$Q_{gs}$	$V_{DD}=50\text{ V}, I_D=1.8\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	0.8	1.2	nC
Gate to drain charge	$Q_{gd}$		-	2.7	4.0	
Gate charge total	$Q_g$		-	6.2	9.3	
Gate plateau voltage	$V_{plateau}$		-	4.1	-	V

**Reverse Diode**

Diode continuous forward current	$I_S$	$T_A=25\text{ }^\circ\text{C}$	-	-	1.8	A
Diode pulse current	$I_{S,pulse}$		-	-	7.3	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=1.8\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.82	1.1	V
Reverse recovery time	$t_{rr}$	$V_R=50\text{ V}, I_F=1.8\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	33	49.5	ns
Reverse recovery charge	$Q_{rr}$		-	46	69	nC

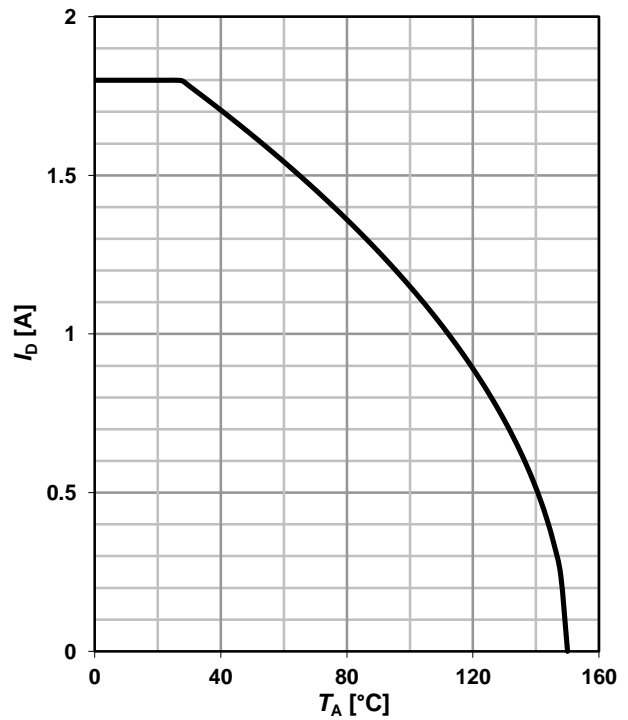
**1 Power dissipation**

$P_{tot}=f(T_A)$



**2 Drain current**

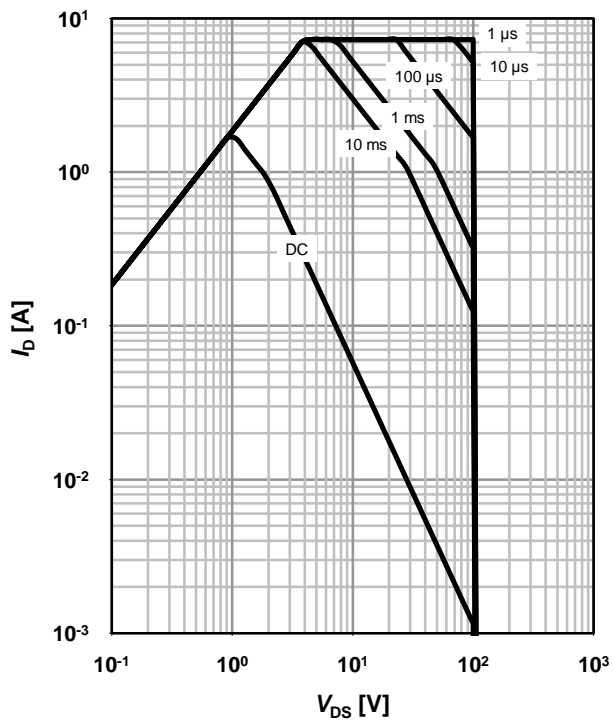
$I_D=f(T_A); V_{GS} \geq 10\text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_A=25\text{ °C}; D=0$

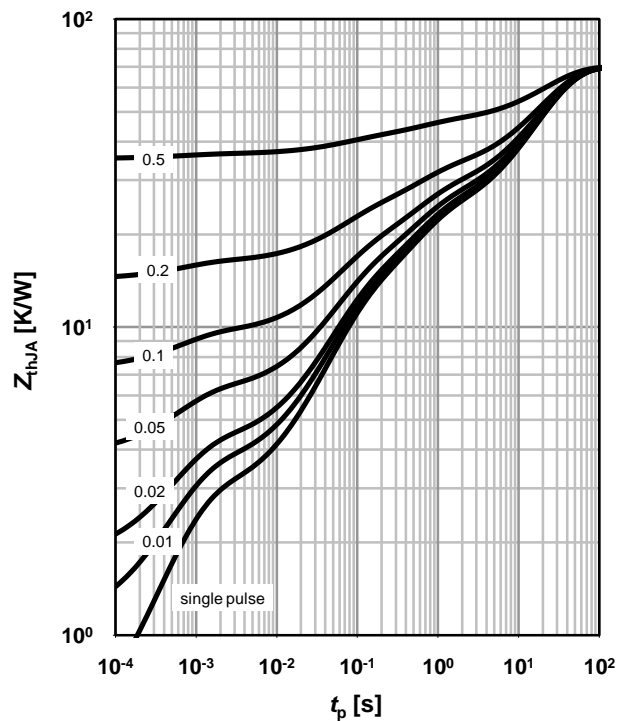
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJA}=f(t_p)$

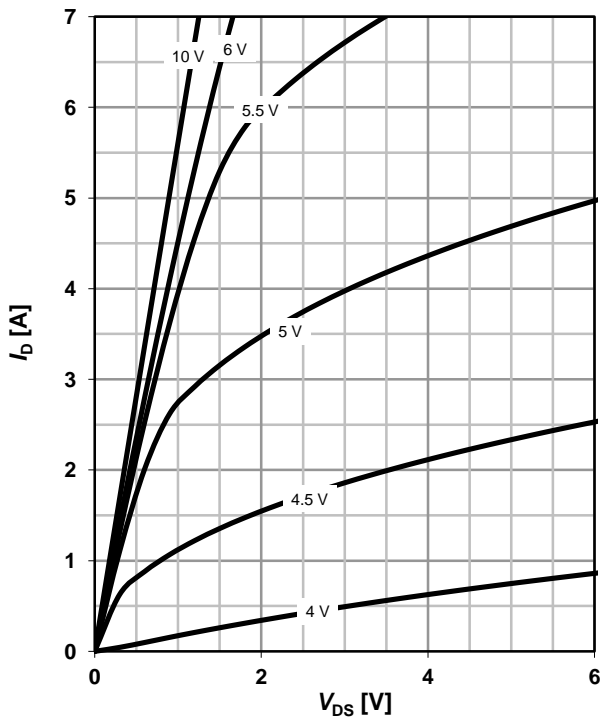
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C}$

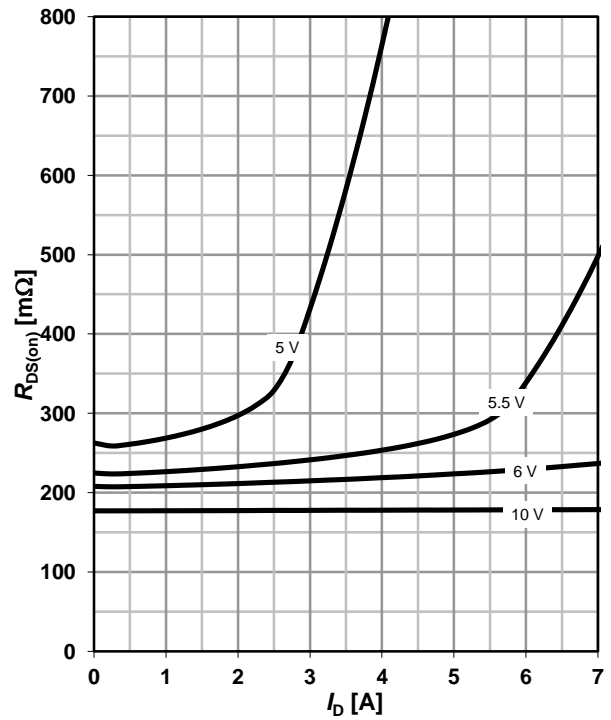
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

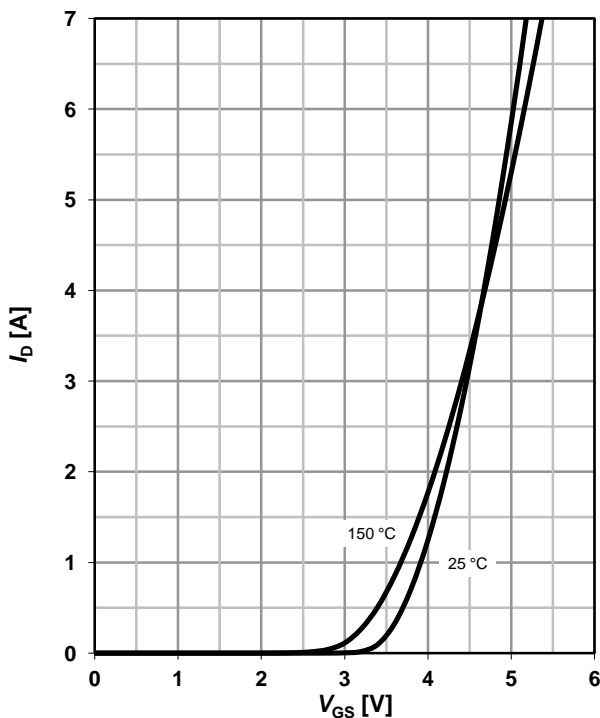
$R_{DS(on)}=f(I_D); T_j=25\text{ }^\circ\text{C}$

parameter:  $V_{GS}$



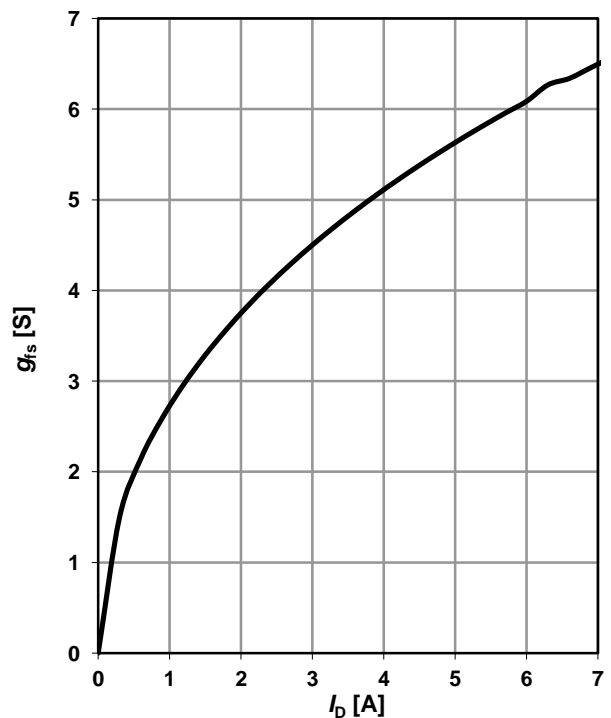
**7 Typ. transfer characteristics**

$I_D=f(V_{GS}); |V_{DS}|>2|I_D|R_{DS(on)max}$



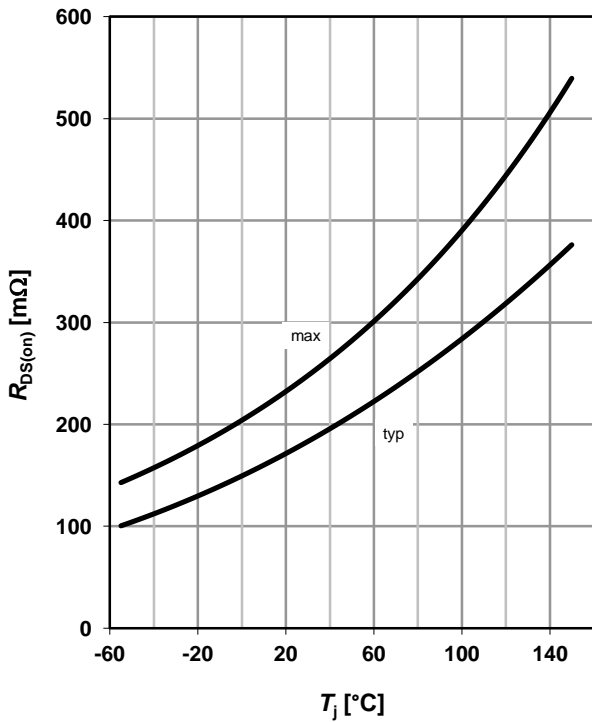
**8 Typ. forward transconductance**

$g_{fs}=f(I_D); T_j=25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

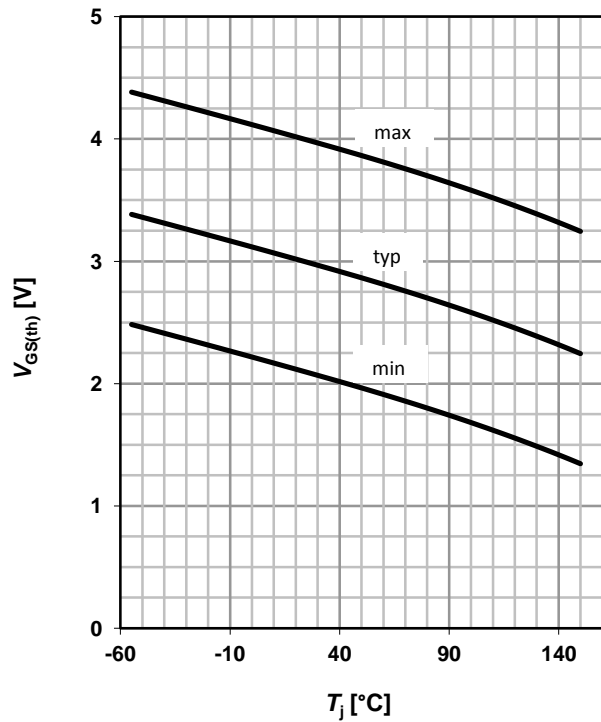
$R_{DS(on)}=f(T_j)$ ;  $I_D=1.8\text{ A}$ ;  $V_{GS}=10\text{ V}$



**10 Typ. gate threshold voltage**

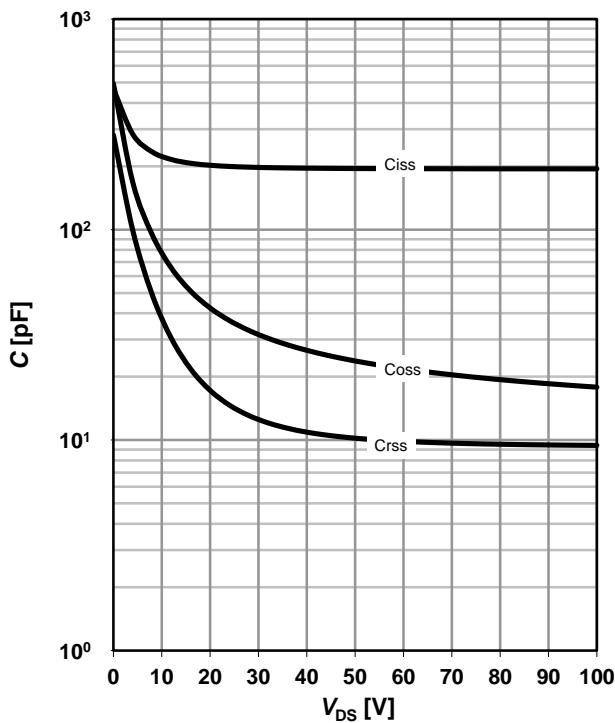
$V_{GS(th)}=f(T_j)$ ;  $V_{DS}=V_{GS}$ ;  $I_D=218\ \mu\text{A}$

parameter:  $I_D$



**11 Typ. capacitances**

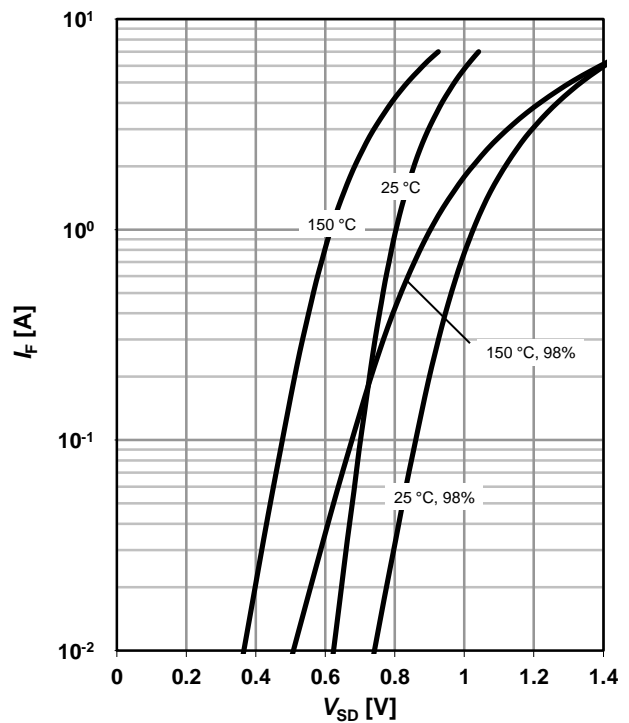
$C=f(V_{DS})$ ;  $V_{GS}=0\text{ V}$ ;  $f=1\text{ MHz}$ ;  $T_j=25^\circ\text{C}$



**12 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

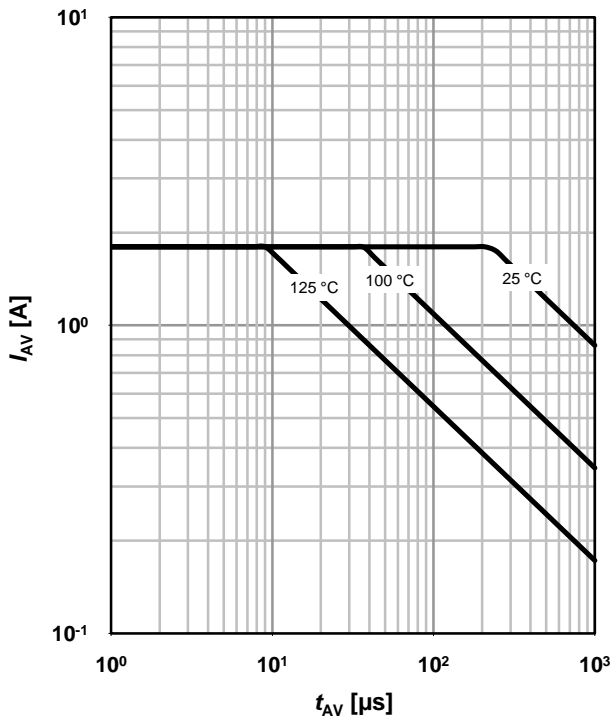
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

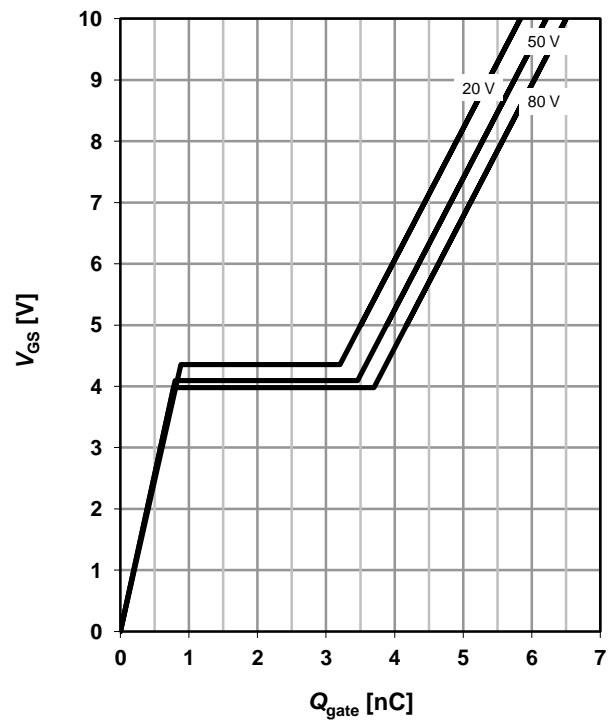
parameter:  $T_{j(\text{start})}$



**14 Typ. gate charge**

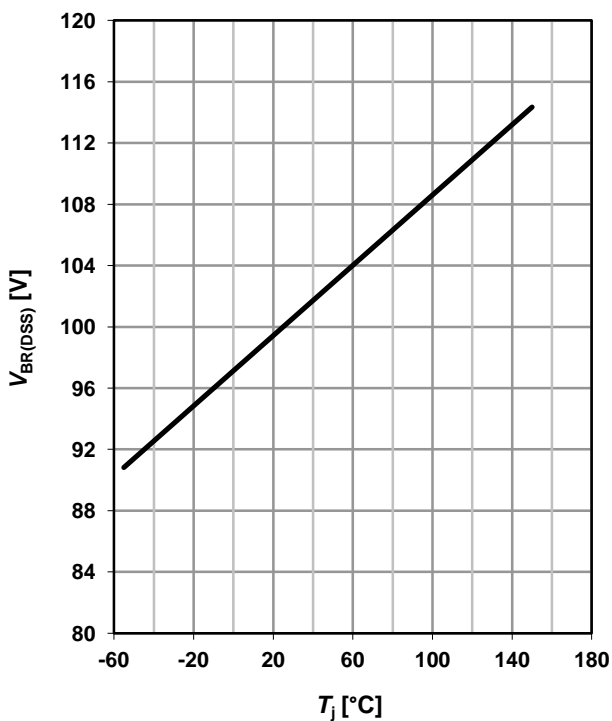
$V_{GS}=f(Q_{\text{gate}}); I_D=1.8 \text{ A pulsed}$

parameter:  $V_{DD}$



**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=250 \mu\text{A}$

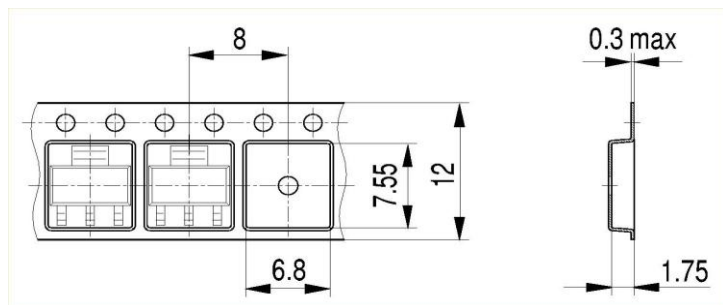
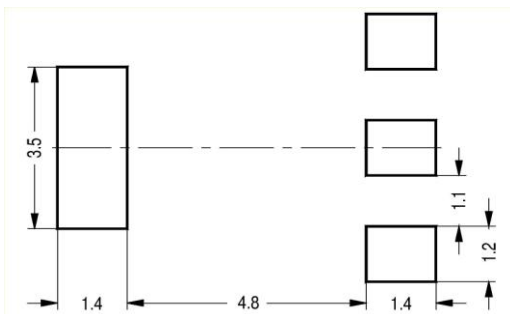
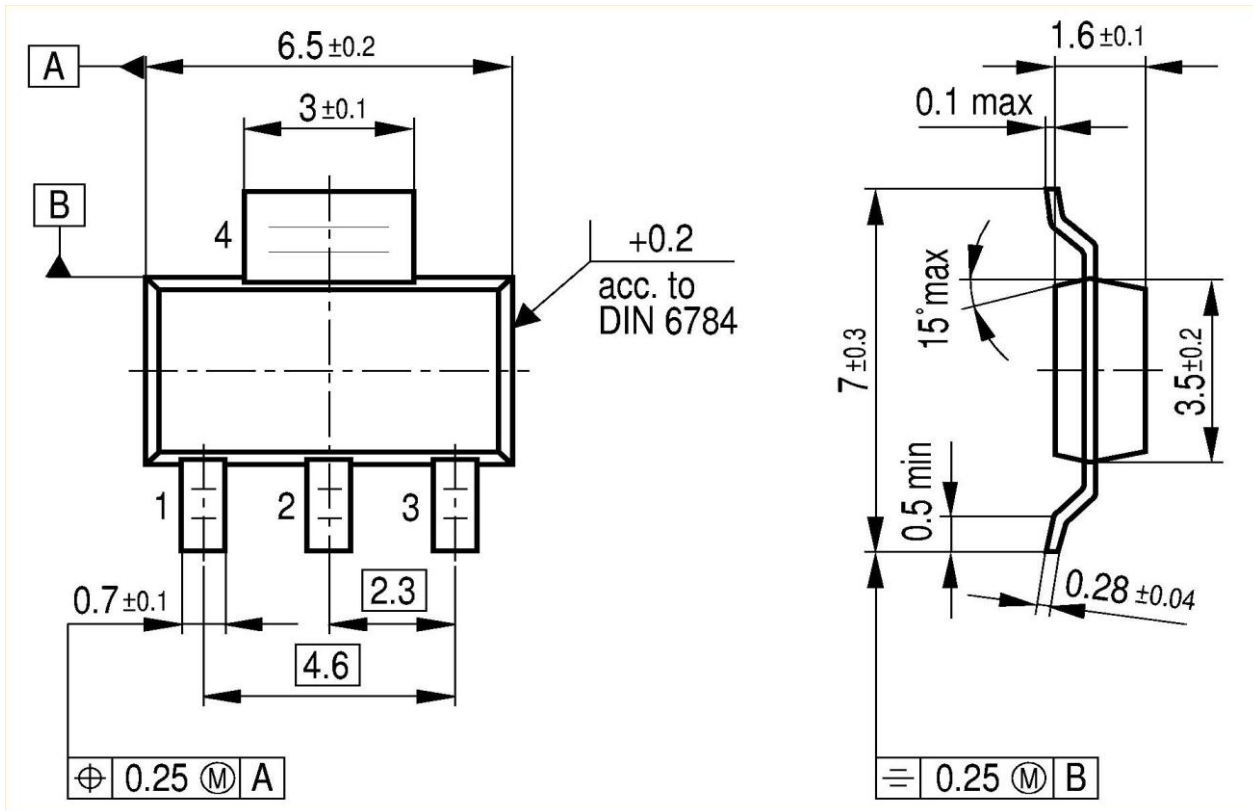


**16 Gate charge waveforms**



SOT223

Package Outline:





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The information given in this document shall in no e  $V_{DD}=50\text{ V}$ ,  $V_{GS}=10\text{ V}$ ,  $I_D=1.8\text{ A}$ ,  $R_G=6\ \Omega$  conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

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